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DATE: Monday, November 01, 2004

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	DB=PC	SPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=ADJ	
	L9	13 and L8	12
	L8	drift region and resurf	309
	L7	16 and 14	0
	L6	(gate insulation film or gate stack or gate insulator of gate insulating film) same (perpendicular or perpendicularly)	252
П	L5	(gate insulation film or gate stack or gate insulator) same (perpendicular or perpendicularly)	464
	L4	11 and 12 and L3	15
	L3	drift region same (perpendicular or perpendicularly) same concentration	39
	L2	base region same (perpendicular or perpendicularly)	648
	L1	(semiconductor or silicon) (wafer or substrate)	446880

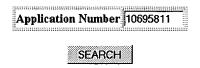
END OF SEARCH HISTORY

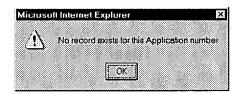
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